

### General Description



The ICS844251I-15 is an Ethernet Clock Generator and a member of the HiPerClocks® family of high performance devices from IDT. The ICS844251I-15 uses an 18pF parallel resonant crystal over the range of 23.2MHz - 30MHz. For Ethernet applications, a 25MHz crystal is used. The device has excellent <1ps phase jitter performance, over the 1.875MHz - 20MHz integration range. The ICS844251I-15 is packaged in a small 8-pin TSSOP, making it ideal for use in systems with limited board space.

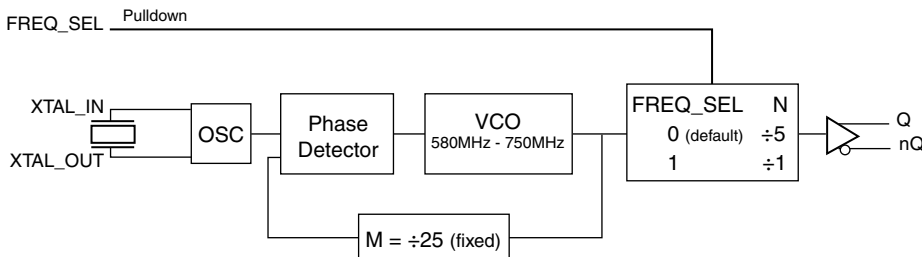
### Features

- One differential LVDS output pair
- Crystal oscillator interface designed for 18pF, parallel resonant crystal (23.2MHz – 30MHz)
- Output frequency ranges: 116MHz – 150MHz and 580MHz – 750MHz
- VCO range: 580MHz – 750MHz
- RMS phase jitter at 125MHz, using a 25MHz crystal (1.875MHz – 20MHz): 0.46ps (typical)
- Full 2.5V output supply mode
- -40°C to 85°C ambient operating temperature
- Available in a lead-free (RoHS 6) package

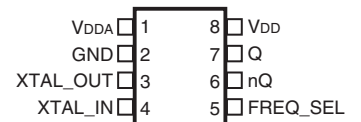
### Common Configuration Table

Inputs					Output Frequency Range (MHz)
Crystal Frequency (MHz)	FREQ_SEL	M	N	Multiplication Value M/N	
25	1	25	1	25	625
26.667	1	25	1	25	666.67
25 (default)	0	25	5	5	125
26.667	0	25	5	5	133.33

### Block Diagram



### Pin Assignment



**ICS844251I-15**  
**8 Lead TSSOP**  
**4.40mm x 3.0mm x 0.925mm**  
**package body**  
**G Package**  
**Top View**

**Table 1. Pin Descriptions**

Number	Name	Type		Description
1	V <sub>DDA</sub>	Power		Analog supply pin.
2	GND	Power		Power supply ground.
3, 4	XTAL_OUT XTAL_IN	Input		Crystal oscillator interface. XTAL_IN is the input, XTAL_OUT is the output.
5	FREQ_SEL	Input	Pulldown	Frequency select pin. LVCMOS/LVTTL interface levels.
6, 7	nQ, Q	Output		Differential output pair. LVDS interface levels.
8	V <sub>DD</sub>	Power		Core supply pin.

NOTE: *Pulldown* refers to internal input resistors. See Table 2, *Pin Characteristics*, for typical values.

**Table 2. Pin Characteristics**

Symbol	Parameter	Test Conditions	Minimum	Typical	Maximum	Units
C <sub>IN</sub>	Input Capacitance			4		pF
R <sub>PULLDOWN</sub>	Input Pulldown Resistor			51		kΩ

## Absolute Maximum Ratings

NOTE: Stresses beyond those listed under *Absolute Maximum Ratings* may cause permanent damage to the device. These ratings are stress specifications only. Functional operation of product at these conditions or any conditions beyond those listed in the *DC Characteristics* or *AC Characteristics* is not implied. Exposure to absolute maximum rating conditions for extended periods may affect product reliability.

Item	Rating
Supply Voltage, $V_{DD}$	4.6V
Inputs, $V_I$	-0.5V to $V_{DD} + 0.5V$
Outputs, $I_O$ Continuous Current Surge Current	10mA 15mA
Package Thermal Impedance, $\theta_{JA}$	129.5°C/W (0 mps)
Storage Temperature, $T_{STG}$	-65°C to 150°C

## DC Electrical Characteristics

**Table 3A. Power Supply DC Characteristics,  $V_{DD} = 2.5V \pm 5\%$ ,  $T_A = -40^\circ C$  to  $85^\circ C$**

Symbol	Parameter	Test Conditions	Minimum	Typical	Maximum	Units
$V_{DD}$	Core Supply Voltage		2.375	2.5	2.625	V
$V_{DDA}$	Analog Supply Voltage		$V_{DD} - 0.10$	2.5	$V_{DD}$	V
$I_{DD}$	Power Supply Current				95	mA
$I_{DDA}$	Analog Supply Current				10	mA

**Table 3B. LVCMOS/LVTTL DC Characteristics,  $V_{DD} = 2.5V \pm 5\%$ ,  $T_A = -40^\circ C$  to  $85^\circ C$**

Symbol	Parameter	Test Conditions	Minimum	Typical	Maximum	Units
$V_{IH}$	Input High Voltage		1.7		$V_{DD} + 0.3$	V
$V_{IL}$	Input Low Voltage		-0.3		0.7	V
$I_{IH}$	Input High Current	$V_{DD} = V_{IN} = 2.625V$			150	$\mu A$
$I_{IL}$	Input Low Current	$V_{DD} = 2.625V, V_{IN} = 0V$	-5			$\mu A$

**Table 3C. LVDS DC Characteristics,  $V_{DD} = 2.5V \pm 5\%$ ,  $T_A = -40^\circ C$  to  $85^\circ C$**

Symbol	Parameter	Test Conditions	Minimum	Typical	Maximum	Units
$V_{OD}$	Differential Output Voltage		247		454	mV
$\Delta V_{OD}$	$V_{OD}$ Magnitude Change				50	mV
$V_{OS}$	Offset Voltage		1.0		1.4	V
$\Delta V_{OS}$	$V_{OS}$ Magnitude Change				50	mV

**Table 4. Crystal Characteristics**

Parameter	Test Conditions	Minimum	Typical	Maximum	Units
Mode of Oscillation		Fundamental			
Frequency		23.2		30	MHz
Equivalent Series Resistance (ESR)				50	$\Omega$
Shunt Capacitance				7	pF

## AC Electrical Characteristics

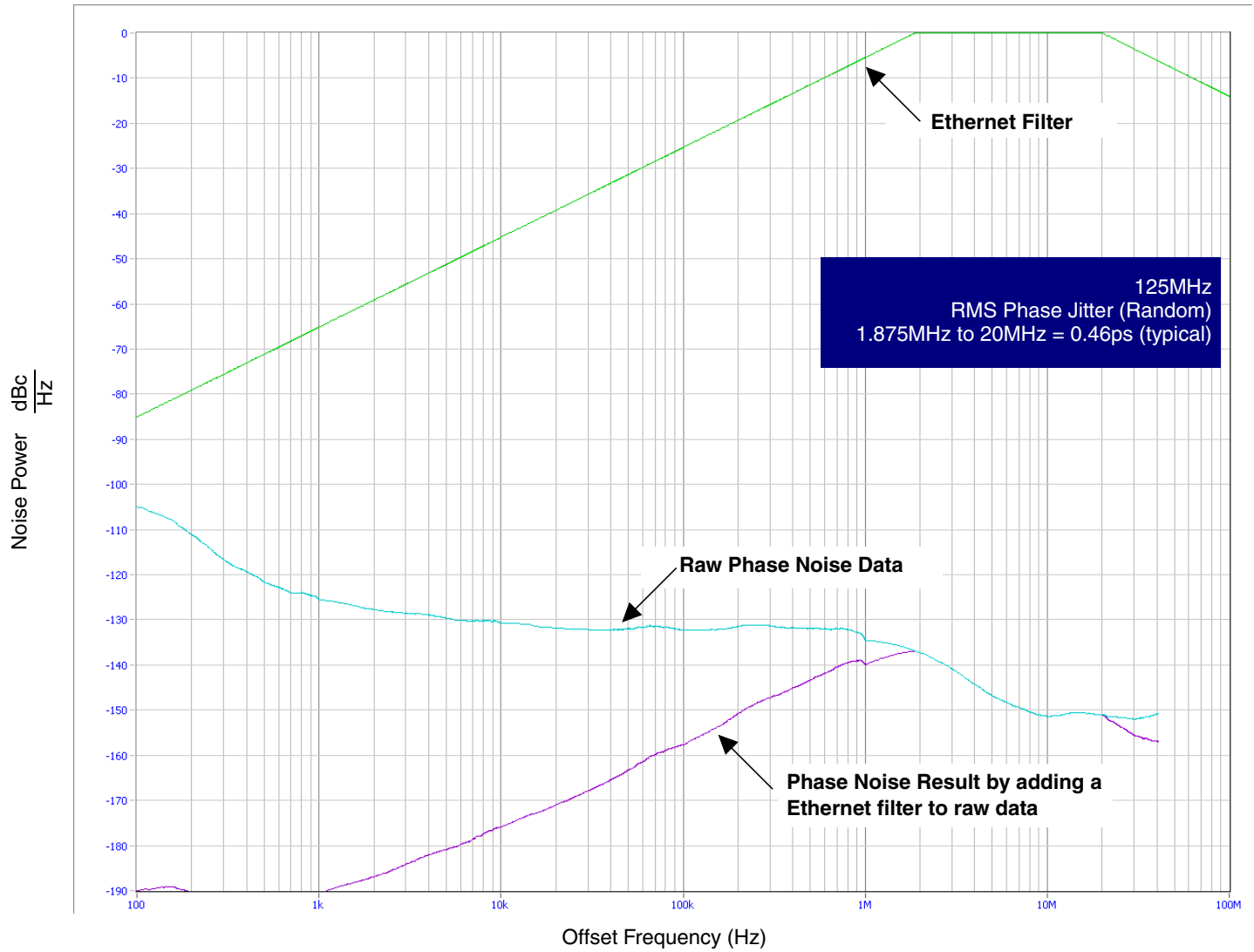
**Table 5. AC Characteristics,  $V_{DD} = 2.5V \pm 5\%$ ,  $T_A = -40^{\circ}C$  to  $85^{\circ}C$** 

Symbol	Parameter	Test Conditions	Minimum	Typical	Maximum	Units
$f_{OUT}$	Output Frequency	FREQ_SEL = 0	116		150	MHz
		FREQ_SEL = 1	580		750	MHz
$f_{jit}(\emptyset)$	RMS Phase Jitter, Random; NOTE 1	125MHz, Integration Range: 1.875MHz – 20MHz		0.46		ps
		625MHz, Integration Range: 1.875MHz – 20MHz		0.35		ps
$t_R / t_F$	Output Rise/Fall Time	20% to 80%	70		550	ps
odc	Output Duty Cycle	FREQ_SEL = 0	48		52	%
		FREQ_SEL = 1	46		54	%

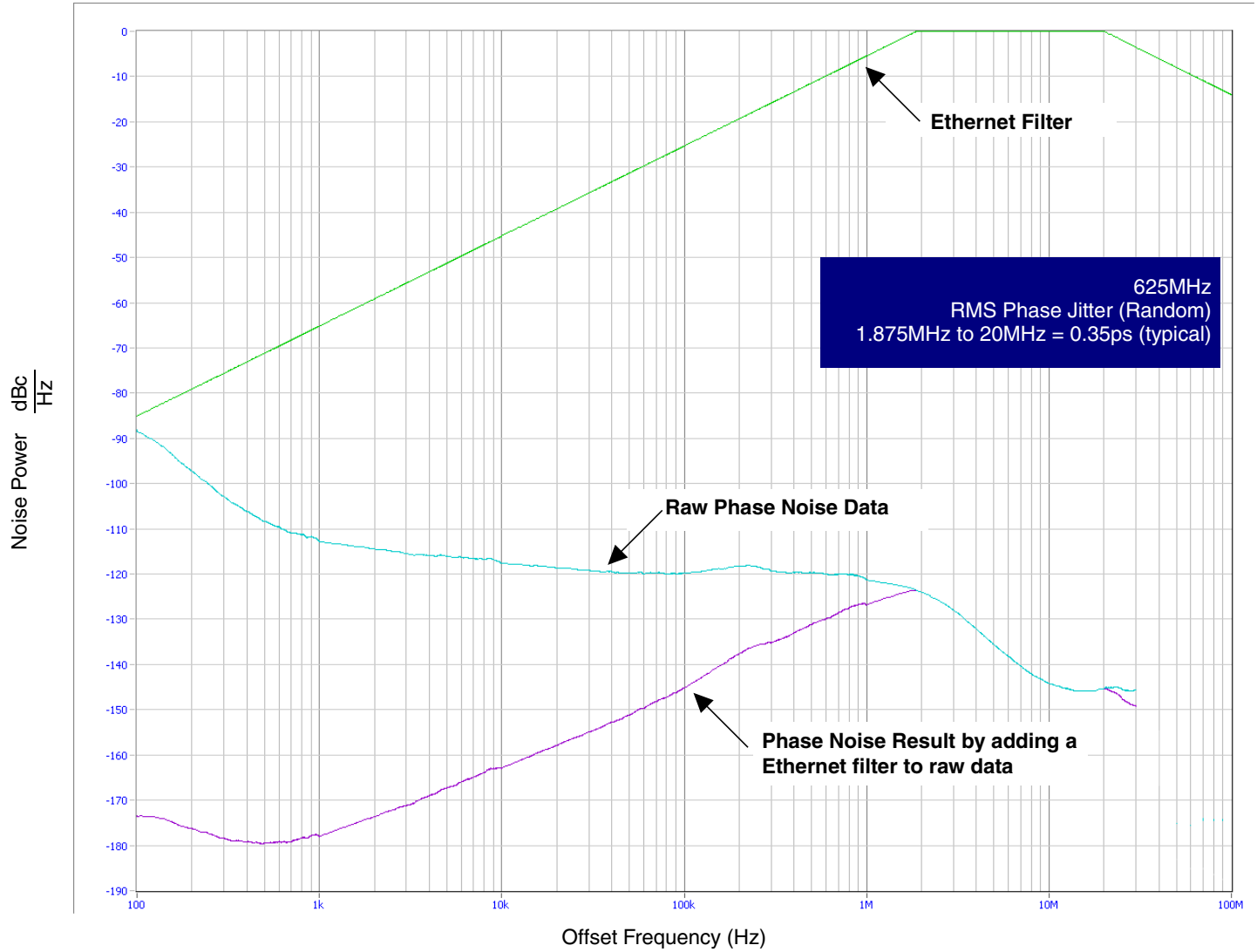
NOTE: Electrical parameters are guaranteed over the specified ambient operating temperature range, which is established when the device is mounted in a test socket with maintained transverse airflow greater than 500 lpm. The device will meet specifications after thermal equilibrium has been reached under these conditions.

NOTE 1: Refer to Phase Noise Plots.

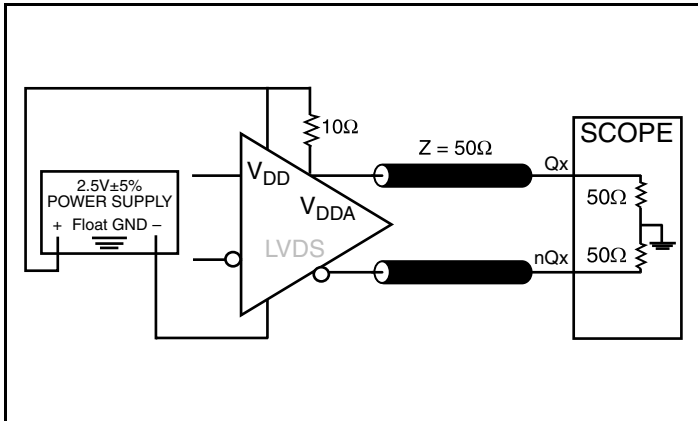
## Typical Phase Noise at 125MHz



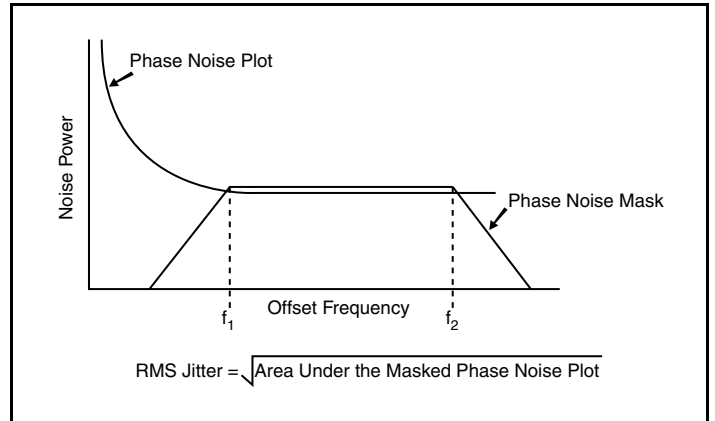
## Typical Phase Noise at 625MHz



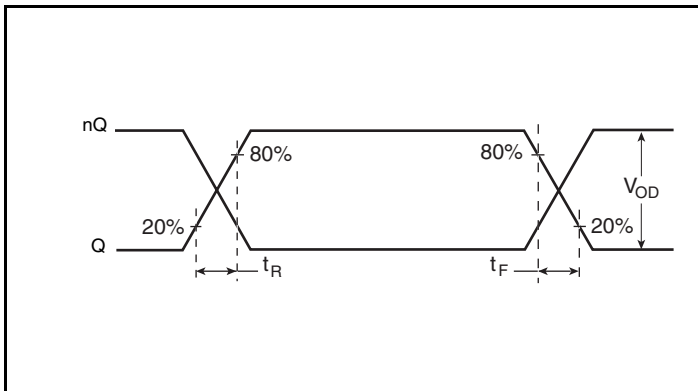
## Parameter Measurement Information



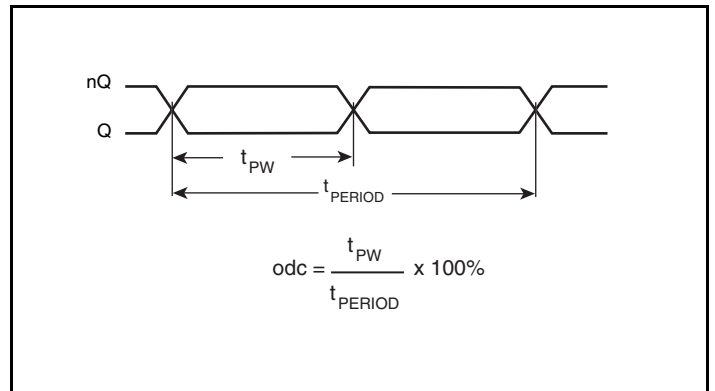
LVDS Output Load AC Test Circuit



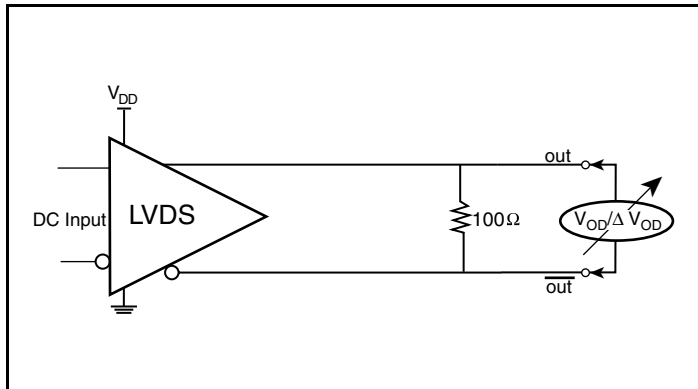
RMS Phase Jitter



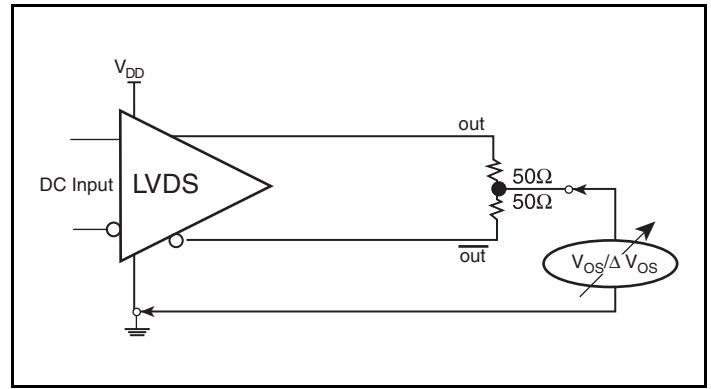
Output Rise/Fall Time



Output Duty Cycle/Pulse Width/Period



Differential Output Voltage Setup

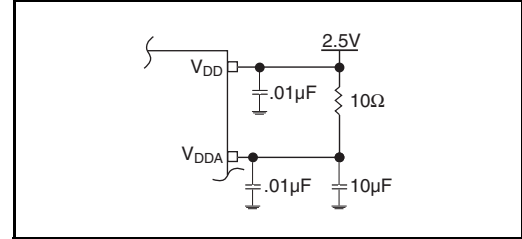


OFFSET VOLTAGE SETUP

## Application Information

### Power Supply Filtering Technique

As in any high speed analog circuitry, the power supply pins are vulnerable to random noise. To achieve optimum jitter performance, power supply isolation is required. The ICS844251I-15 provides separate power supplies to isolate any high switching noise from the outputs to the internal PLL.  $V_{DD}$  and  $V_{DDA}$  should be individually connected to the power supply plane through vias, and  $0.01\mu\text{F}$  bypass capacitors should be used for each pin. *Figure 1* illustrates this for a generic  $V_{DD}$  pin and also shows that  $V_{DDA}$  requires that an additional  $10\Omega$  resistor along with a  $10\mu\text{F}$  bypass capacitor be connected to the  $V_{DDA}$  pin.

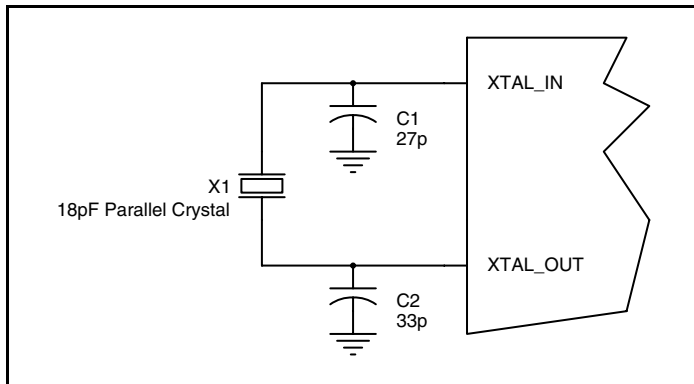


**Figure 1. Power Supply Filtering**

### Crystal Input Interface

The ICS844251I-15 has been characterized with  $18\text{pF}$  parallel resonant crystals. The capacitor values,  $C1$  and  $C2$ , shown in *Figure 2* below were determined using a  $25\text{MHz}$ ,  $18\text{pF}$  parallel resonant

crystal and were chosen to minimize the ppm error. The optimum  $C1$  and  $C2$  values can be slightly adjusted for different board layouts.



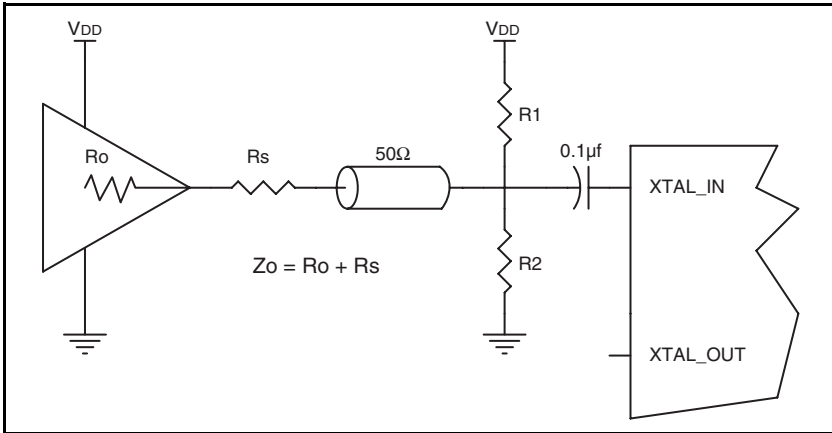
**Figure 2. Crystal Input Interface**



### LVC MOS to XTAL Interface

The XTAL\_IN input can accept a single-ended LVC MOS signal through an AC coupling capacitor. A general interface diagram is shown in *Figure 3*. The XTAL\_OUT pin can be left floating. The input edge rate can be as slow as 10ns. For LVC MOS inputs, it is recommended that the amplitude be reduced from full swing to half swing in order to prevent signal interference with the power rail and to reduce noise. This configuration requires that the output impedance of the driver ( $R_o$ ) plus the series resistance ( $R_s$ ) equals

the transmission line impedance. In addition, matched termination at the crystal input will attenuate the signal in half. This can be done in one of two ways. First,  $R_1$  and  $R_2$  in parallel should equal the transmission line impedance. For most 50Ω applications,  $R_1$  and  $R_2$  can be 100Ω. This can also be accomplished by removing  $R_1$  and making  $R_2$  50Ω. By overdriving the crystal oscillator, the device will be functional, but note, the device performance is guaranteed by using a quartz crystal.

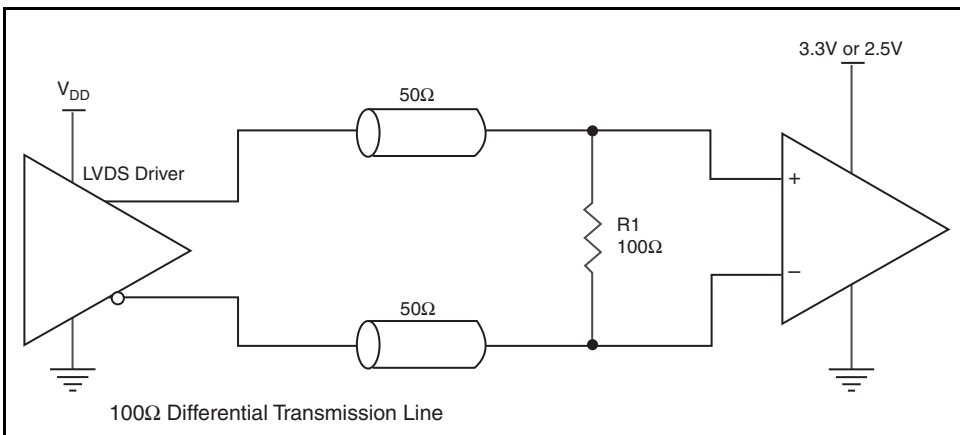


**Figure 3. General Diagram for LVC MOS Driver to XTAL Input Interface**

### 2.5V LVDS Driver Termination

*Figure 4* shows a typical termination for LVDS driver in characteristic impedance of 100Ω differential (50Ω single) transmission line

environment. For buffer with multiple LVDS driver, it is recommended to terminate the unused outputs.



**Figure 4. Typical LVDS Driver Termination**

## Power Considerations

This section provides information on power dissipation and junction temperature for the ICS844251I-15. Equations and example calculations are also provided.

### 1. Power Dissipation.

The total power dissipation for the ICS844251I-15 is the sum of the core power plus the analog power plus the power dissipated in the load(s). The following is the power dissipation for  $V_{DD} = 2.5V + 5\% = 2.625V$ , which gives worst case results.

NOTE: Please refer to Section 3 for details on calculating power dissipated in the load.

- Power (core)<sub>MAX</sub> =  $V_{DD\_MAX} * (I_{DD\_MAX} + I_{DDA\_MAX}) = 2.625V * (100mA + 10mA) = \mathbf{288.75mW}$

### 2. Junction Temperature.

Junction temperature,  $T_j$ , is the temperature at the junction of the bond wire and bond pad directly affects the reliability of the device. The maximum recommended junction temperature for HiPerClockS devices is 125°C. Limiting the internal transistor junction temperature,  $T_j$ , to 125°C ensures that the bond wire and bond pad temperature remains below 125°C.

The equation for  $T_j$  is as follows:  $T_j = \theta_{JA} * Pd\_total + T_A$

$T_j$  = Junction Temperature

$\theta_{JA}$  = Junction-to-Ambient Thermal Resistance

$Pd\_total$  = Total Device Power Dissipation (example calculation is in section 1 above)

$T_A$  = Ambient Temperature

In order to calculate junction temperature, the appropriate junction-to-ambient thermal resistance  $\theta_{JA}$  must be used. Assuming no air flow and a multi-layer board, the appropriate value is 129.5°C/W per Table 6 below.

Therefore,  $T_j$  for an ambient temperature of 85°C with all outputs switching is:

$$85^\circ\text{C} + 0.289\text{W} * 129.5^\circ\text{C/W} = 122.4^\circ\text{C}. \text{ This is below the limit of } 125^\circ\text{C}.$$

This calculation is only an example.  $T_j$  will obviously vary depending on the number of loaded outputs, supply voltage, air flow and the type of board (multi-layer).

**Table 6. Thermal Resistance  $\theta_{JA}$  for 8 Lead TSSOP, Forced Convection**

Meters per Second	$\theta_{JA}$ by Velocity		
	0	1	2.5
Multi-Layer PCB, JEDEC Standard Test Boards	129.5°C/W	125.5°C/W	123.5°C/W

## Reliability Information

Table 7.  $\theta_{JA}$  vs. Air Flow Table for a 8 Lead TSSOP

$\theta_{JA}$ vs. Air Flow			
Meters per Second	0	1	2.5
Multi-Layer PCB, JEDEC Standard Test Boards	129.5°C/W	125.5°C/W	123.5°C/W

## Transistor Count

The transistor count for ICS844251I-15 is: 2398

## Package Outline and Package Dimensions

Package Outline - G Suffix for 8 Lead TSSOP

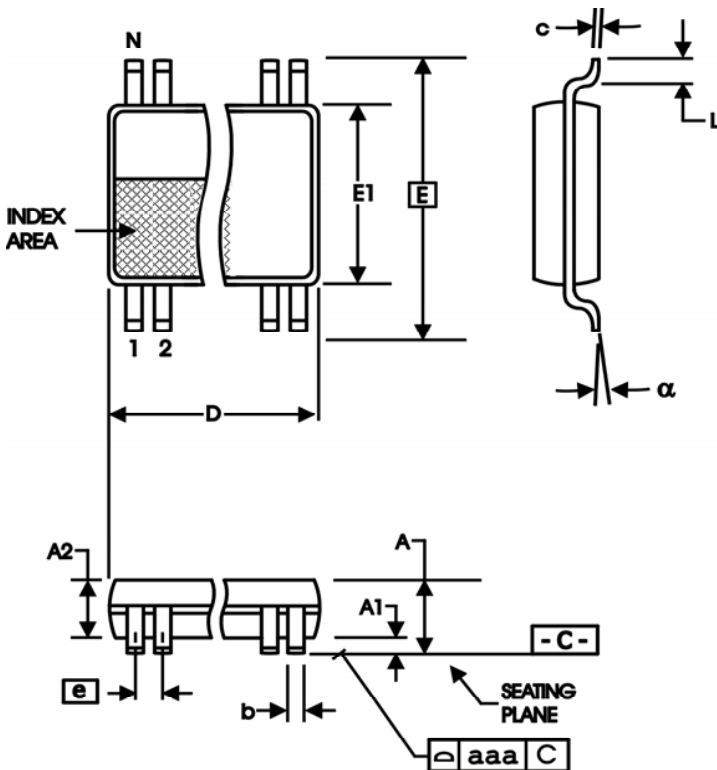


Table 8. Package Dimensions

All Dimensions in Millimeters		
Symbol	Minimum	Maximum
N	8	
A		1.20
A1	0.5	0.15
A2	0.80	1.05
b	0.19	0.30
c	0.09	0.20
D	2.90	3.10
E	6.40 Basic	
E1	4.30	4.50
e	0.65 Basic	
L	0.45	0.75
α	0°	8°
aaa		0.10

Reference Document: JEDEC Publication 95, MO-153

## Ordering Information

Table 9. Ordering Information

Part/Order Number	Marking	Package	Shipping Packaging	Temperature
844251BGI-15LF	BI15L	"Lead-Free" 8 Lead TSSOP	Tube	-40°C to 85°C
844251BGI-15LFT	BI15L	"Lead-Free" 8 Lead TSSOP	2500 Tape & Reel	-40°C to 85°C

NOTE: Parts that are ordered with an "LF" suffix to the part number are the Pb-Free configuration and are RoHS compliant.



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